

- ✓ 28. The semiconductor structure of Claim 19, wherein the conductive element is a gate electrode.
- ✓ 29. The semiconductor structure of Claim 28, further comprising a gate dielectric layer located between the semiconductor substrate and the gate electrode.
- ✓ 30. The semiconductor structure of Claim 19, further comprising a source/drain region located in the semiconductor substrate, wherein the silicide strap contacts the source/drain region.
C cont
- ✓ 31. The semiconductor structure of Claim 19, wherein the dielectric spacer comprises silicon oxide or silicon nitride.
- ✓ 32. The semiconductor structure of Claim 19, wherein the silicide strap comprises cobalt silicide.
D cont
- ✓ 33. The semiconductor structure of Claim 21, wherein the silicide strap comprises a refractory metal layer reacted with the semiconductor region.
- ✓ 34. The semiconductor structure of Claim 21, wherein the conductive element is a gate electrode.
- ✓ 35. The semiconductor structure of Claim 34, further comprising a gate dielectric layer located between the semiconductor substrate and the gate electrode.
- ✓ 36. The semiconductor structure of Claim 21, further comprising a source/drain region located in the

semiconductor substrate, wherein the silicide strap contacts the source/drain region.

C' cont

37. The semiconductor structure of Claim 21, wherein the dielectric spacer comprises silicon oxide or silicon nitride.

D' cont

38. The semiconductor structure of Claim 21, wherein the silicide strap comprises cobalt silicide.--